

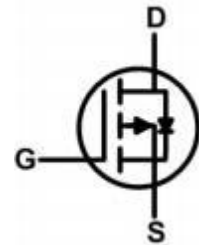
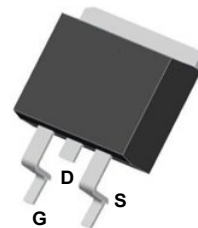
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology


Product Summary

BVDSS	RDS(on)	ID
-40V	3.1mΩ	-150A

Description

The XXW150P04G is the high cell density trench P-ch MOSFETs, which provide excellent RDS(on) and gate charge for most of the synchronous buck converter applications. The XXW150P04G meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO263 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	-150	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	-105	A
I_{DM}	Pulsed Drain Current ²	-592	A
EAS	Single Pulse Avalanche Energy ³	1225	mJ
I_{AS}	Avalanche Current	---	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	200	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	---	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.95	$^{\circ}C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-40	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1\text{mA}$	---	---	---	$V/^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-20A$	---	3.1	4.1	$\text{m}\Omega$
		$V_{GS}=-4.5V, I_D=-20A$	---	4.4	5.4	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2	---	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	$\text{mV}/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-40V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-40V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	-100	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-10V, I_D=-20A$	---	51	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	1.7	---	Ω
Q_g	Total Gate Charge	$V_{DS}=-20V, V_{GS}=-10V, I_D=-20A$	---	195	---	nC
Q_{gs}	Gate-Source Charge		---	24.1	---	
Q_{gd}	Gate-Drain Charge		---	39.9	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-20V, V_{GS}=-10V, R_G=3.3\Omega$	---	19.6	---	ns
T_r	Rise Time		---	3.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	22.8	---	
T_f	Fall Time		---	38	---	
C_{iss}	Input Capacitance	$V_{DS}=-20V, V_{GS}=0V, f=1\text{MHz}$	---	10733	---	pF
C_{oss}	Output Capacitance		---	770	---	
C_{rss}	Reverse Transfer Capacitance		---	697	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	-150	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=-20A, T_J=25^\circ\text{C}$	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	$I_F=-20A, di/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	51.1	---	nS
Q_{rr}	Reverse Recovery Charge		---	125.2	---	nC

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

3. The EAS data shows Max. rating. The test condition is $T_J=25^\circ\text{C}, V_{DD}=-40V, V_G=-10V, R_g=25\Omega, L=0.5\text{mH}$.

4. The power dissipation is limited by 150°C junction temperature

5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

Typical Electrical And Thermal Characteristics (Curves)

Figure 1. Output Characteristics

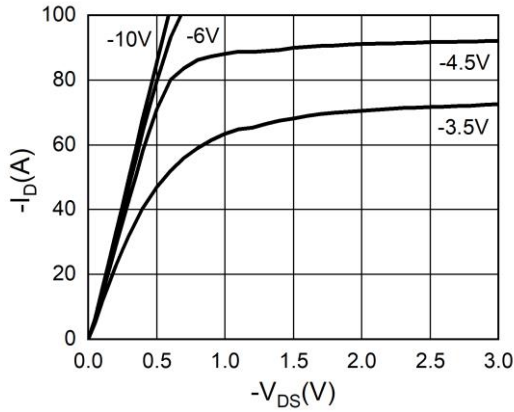


Figure 2. Transfer Characteristics

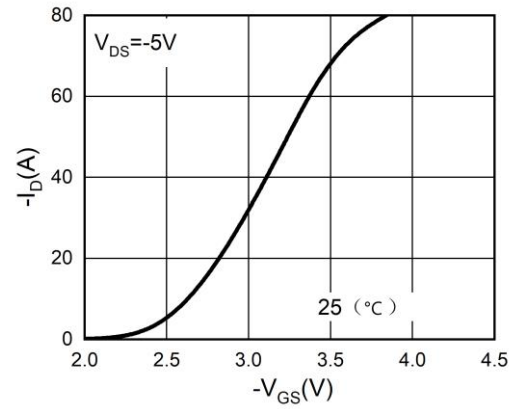


Figure 3. Power Dissipation

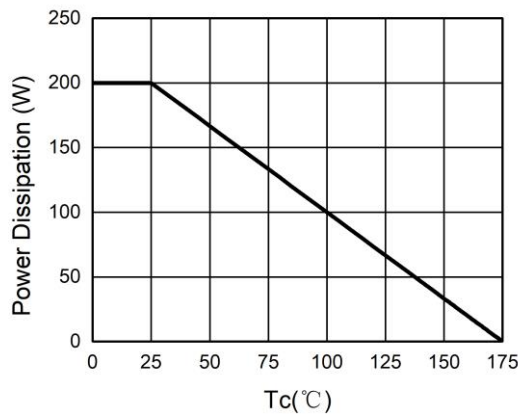


Figure 4. Drain Current

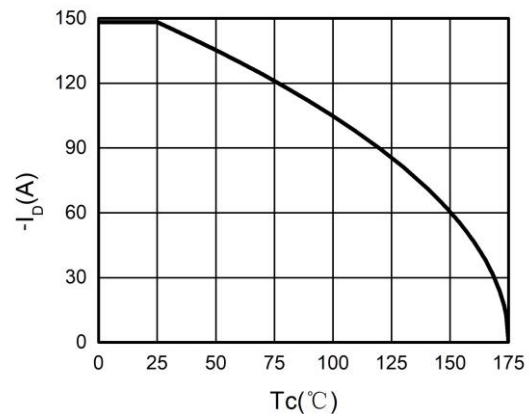


Figure 5. BV_{DSS} vs Junction Temperature

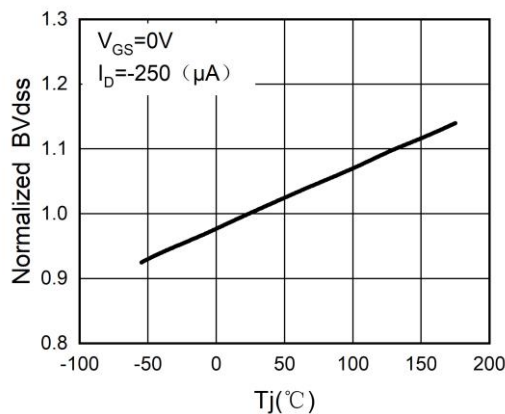
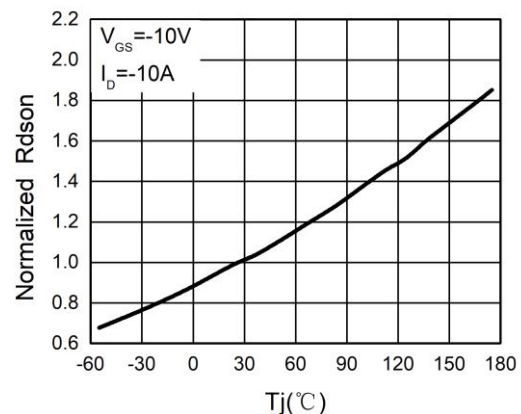


Figure 6. $R_{DS(ON)}$ vs Junction Temperature



Typical Electrical And Thermal Characteristics (Curves)

Figure 7. Gate Charge Waveforms

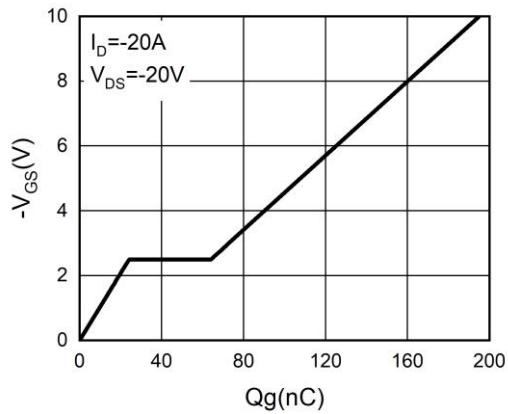


Figure 8. Capacitance

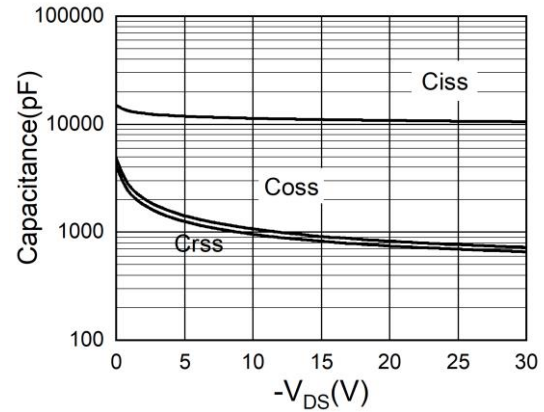


Figure 9. Body-Diode Characteristics

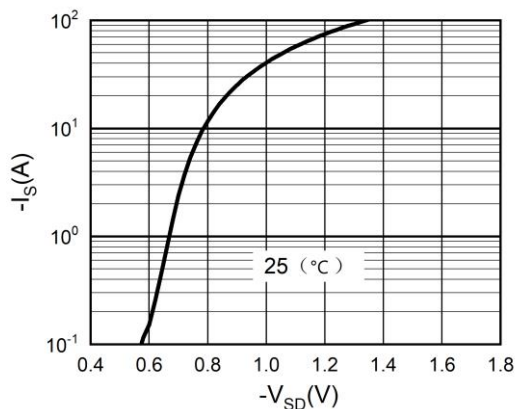
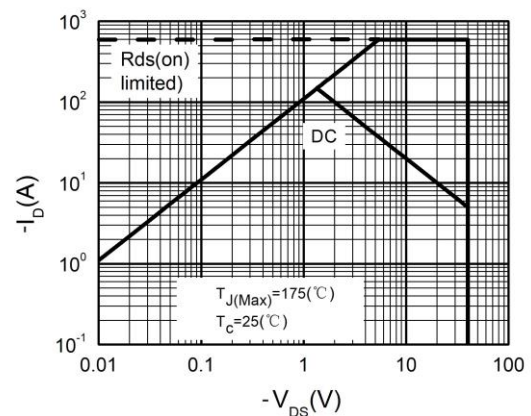
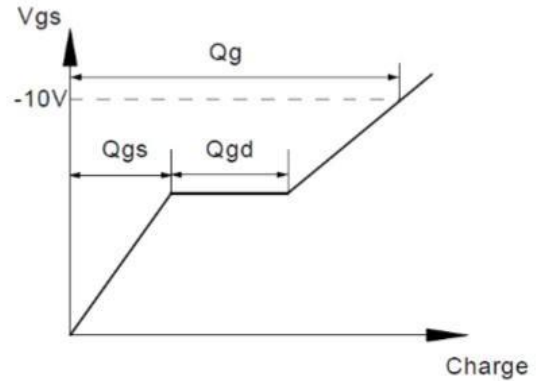
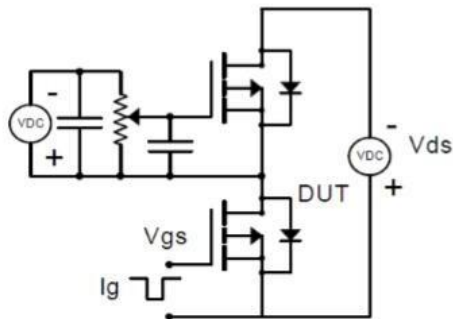


Figure 10. Maximum Safe Operating Area

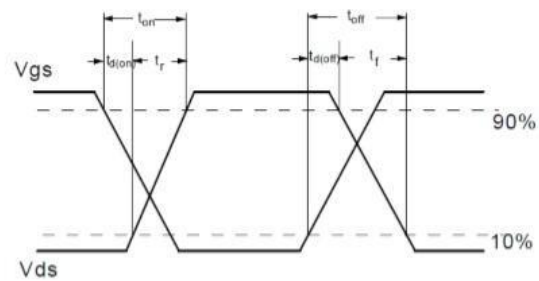
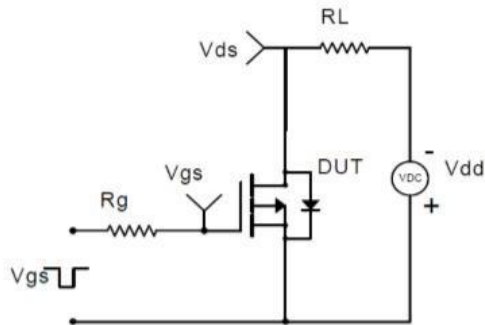


Test Circuit

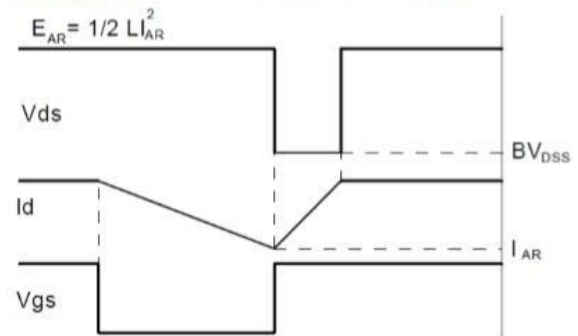
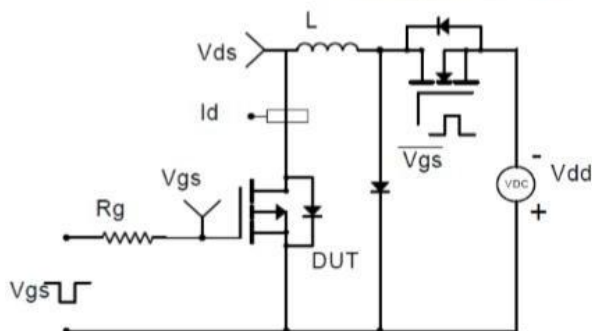
Gate Charge Test Circuit & Waveform



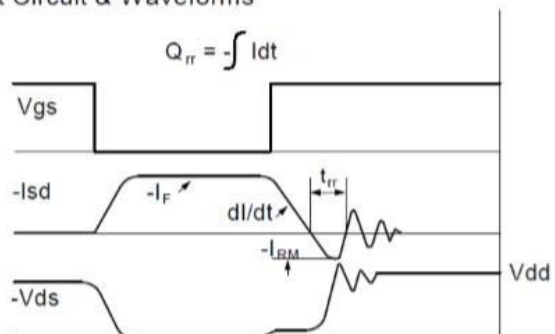
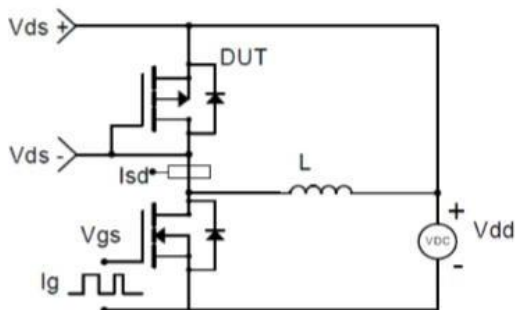
Resistive Switching Test Circuit & Waveforms



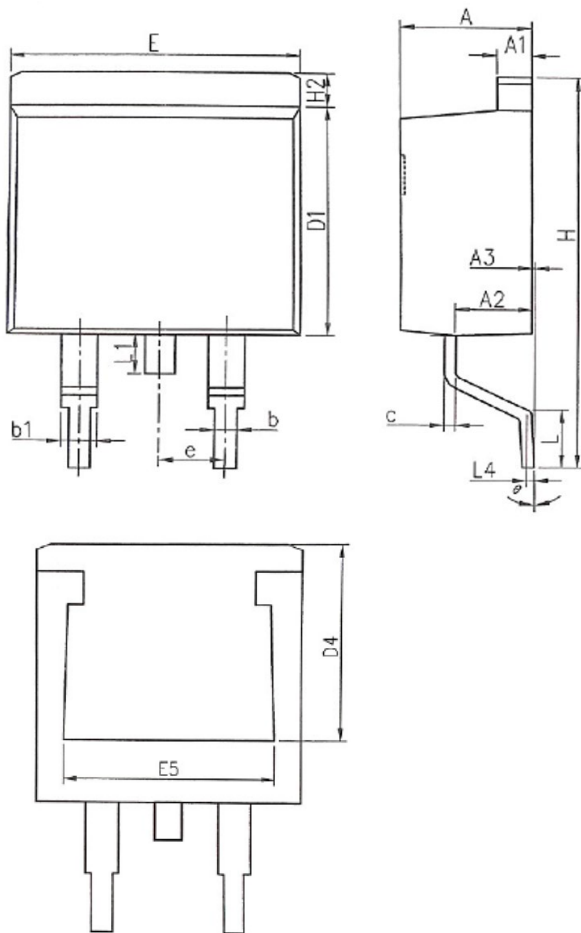
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Mechanical Dimensions for TO-263



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	4.37	4.89
A1	1.17	1.42
A2	2.20	2.90
A3	0.00	0.25
b	0.70	0.96
b1	1.17	1.47
c	0.28	0.60
D1	8.45	9.30
D4	6.60	-
E	9.80	10.40
E5	7.06	-
e	2.54BSC	
H	14.70	15.70
H2	1.07	1.47
L	2.00	2.80
L1	-	1.75
L4	0.254BSC	
θ	0°	9°